Abstracts

A 1.75 - 6 GHz Miniaturized GaAs FET Amplifier Using Quasi-Lumped Element Impedance Matching Networks

S.B. Moghe, R.E. Gray and W.C. Tsai. "A 1.75 - 6 GHz Miniaturized GaAs FET Amplifier Using Quasi-Lumped Element Impedance Matching Networks." 1981 MTT-S International Microwave Symposium Digest 81.1 (1981 [MWSYM]): 316-318.

A quasi-lumped element impedance matching technique was developed for a multi-octave bandwidth FET amplifier. The lumped elements were realized by parallel capacitors, high impedance band wires and etched lines on a 0.170 x 0.085 x 0.010 inch alumina substrate. A two-stage amplifier has been constructed using this method and yields 17± dB gain and 3.5 dB maximum noise figure over 1.75 to 6.0 GHz band.

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